

## 2N3415



## **NPN General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	25	V
V <sub>CBO</sub>	Collector-Base Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3415	
$P_D$	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# NPN General Purpose Amplifier (continued)

Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	25		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	25		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0	5.0		V
Ісво	Collector-Cutoff Current	V <sub>CB</sub> = 25 V, I <sub>E</sub> = 0 V <sub>CB</sub> = 25 V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C		0.1 15	μA μA
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		0.1	μΑ
	RACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 4.5 \text{ V}, I_{C} = 2.0 \text{ mA}$	180	540	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$		0.3	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$	0.6	1.3	V
SMALL S	IGNAL CHARACTERISTICS				
h <sub>fe</sub>	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V},$ f = 1.0  kHz	180		

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

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